

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Volt Drop
- Isolated Cu Base with Al₂O₃ Substrates
- Dual Diodes can be paralleled for 2400A Rating
- Lead Free Construction

APPLICATIONS

- Chopper Diodes
- Boost and Buck Circuits
- Free-wheel Circuits
- Multi-level Switch Inverters

The DFM1200FXS12-A000 is a dual 1200V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM1200FXS12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{RRM}		1200V
V_F	(typ)	1.9V
I_F	(max)	1200A
I_{FM}	(max)	2400A

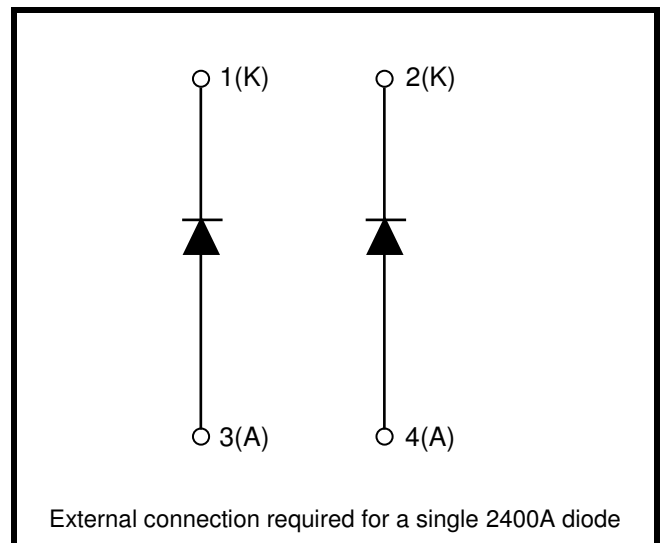
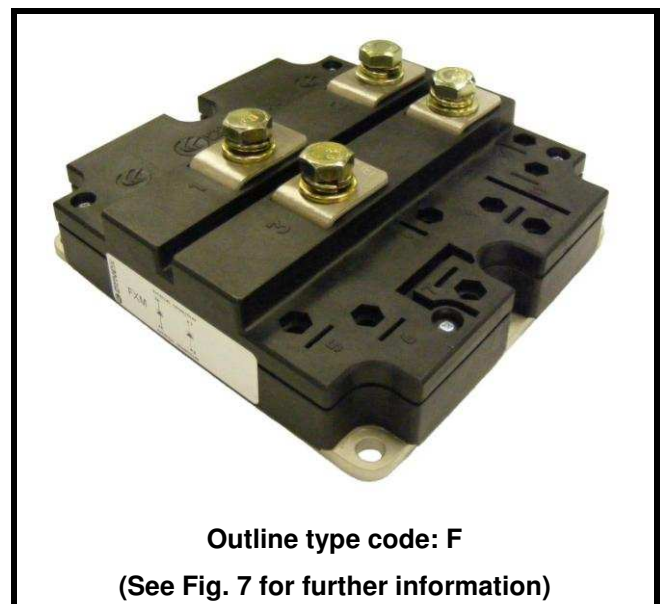


Fig. 1 Circuit configuration



Outline type code: F
(See Fig. 7 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{\text{case}} = 25\text{ °C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage	$T_j = 125\text{ °C}$	1200	V
I_F	Forward current (per arm)	DC, $T_{\text{case}} = 75\text{ °C}$, $T_j = 125\text{ °C}$	1200	A
I_{FM}	Max. forward current	$T_{\text{case}} = 110\text{ °C}$, $t_p = 1\text{ ms}$	2400	A
I^2t	I^2t value fuse current rating	$V_R = 0$, $t_p = 10\text{ ms}$, $T_j = 125\text{ °C}$	200	kA^2s
P_{max}	Max. transistor power dissipation	$T_{\text{case}} = 25\text{ °C}$, $T_j = 125\text{ °C}$	5000	W
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	Al_2O_3
Baseplate material:	Cu
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	350

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{\text{th}(j-c)}$	Thermal resistance (per arm)	Continuous dissipation – junction to case	-	-	20	°C/kW
$R_{\text{th}(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	8	°C/kW
T_j	Junction temperature		-	-	125	°C
T_{stg}	Storage temperature range		-40	-	125	°C
	Screw Torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M8	-	-	10	Nm

STATIC ELECTRICAL CHARACTERISTICS – PER ARM
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{RM}	Peak reverse current	V _R = 1200V, T _j = 125°C			30	mA
V _F	Forward voltage	I _F = 1200A		1.9	2.2	V
		I _F = 1200A, T _j = 125°C		2.1	2.4	V
L _M	Inductance			20		nH

STATIC ELECTRICAL CHARACTERISTICS
T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
L _M	Module inductance (externally connected in parallel)			15		nH

DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM
T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q _{rr}	Reverse recovery charge	I _F = 1200A V _R = 600V di _F /dt = 9000A/μs		200		μC
I _{rr}	Peak reverse recovery current			800		A
E _{rec}	Reverse recovery energy			80		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
Q _{rr}	Reverse recovery charge	I _F = 1200A V _R = 600V di _F /dt = 8400A/μs		300		μC
I _{rr}	Peak reverse recovery current			920		A
E _{rec}	Reverse recovery energy			140		mJ

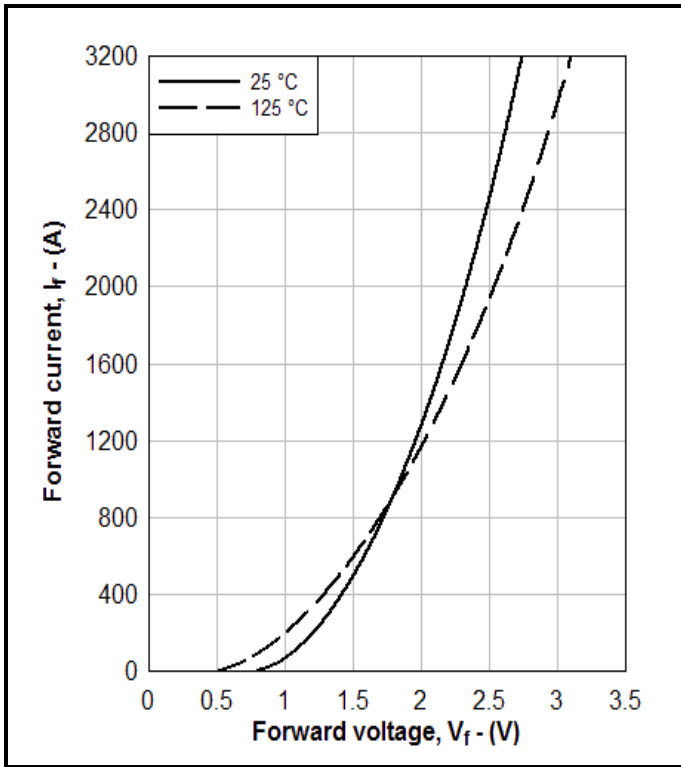


Fig. 3 Diode typical forward characteristics

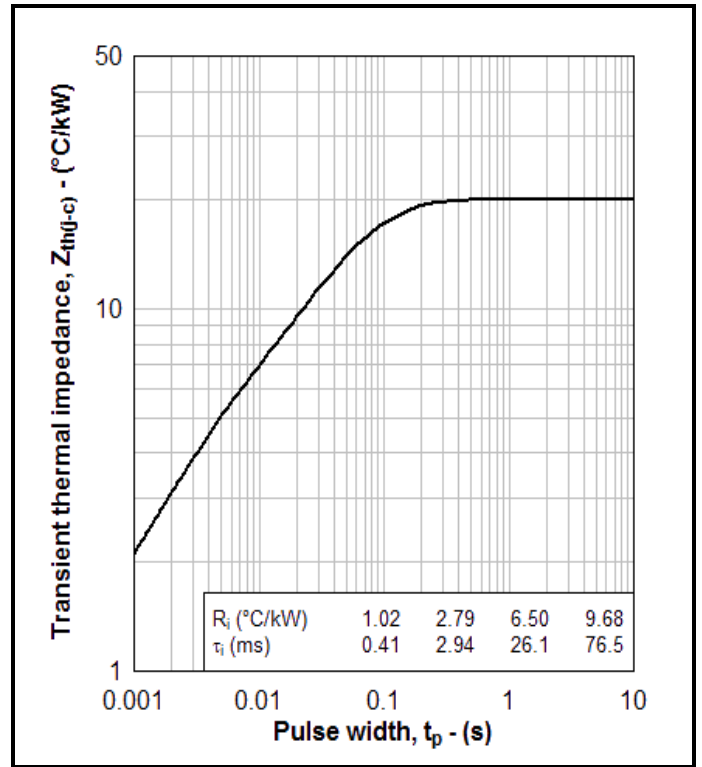


Fig. 4 Transient thermal impedance

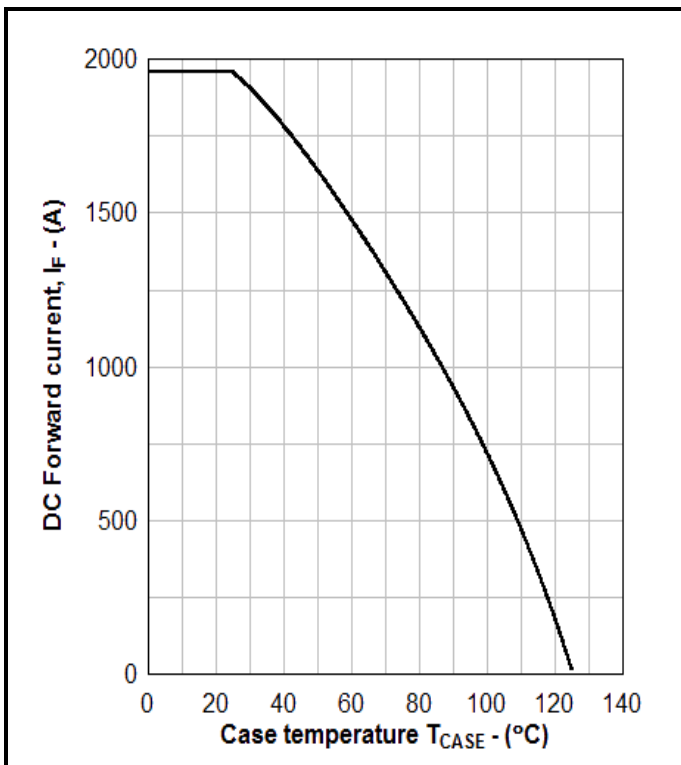


Fig. 5 DC Current rating vs case temperature

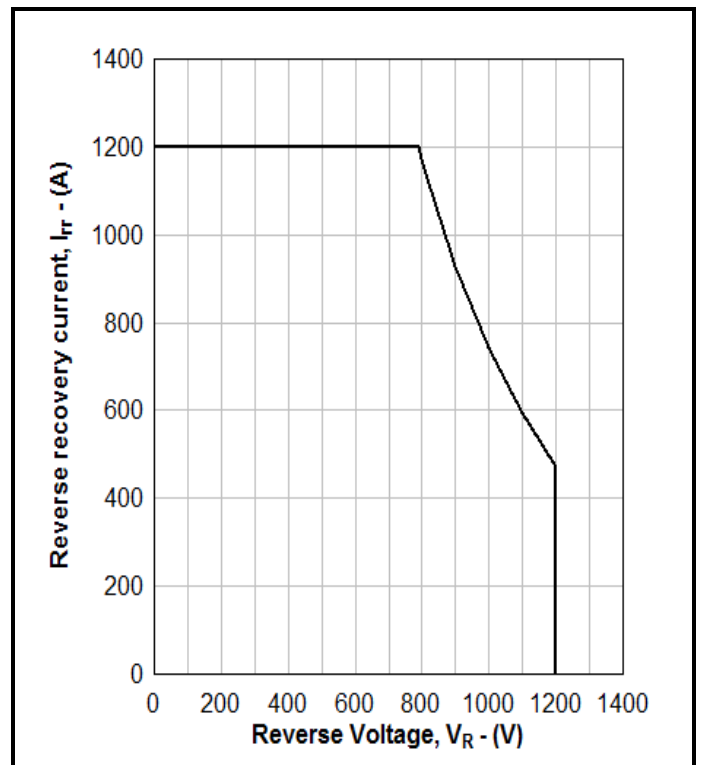
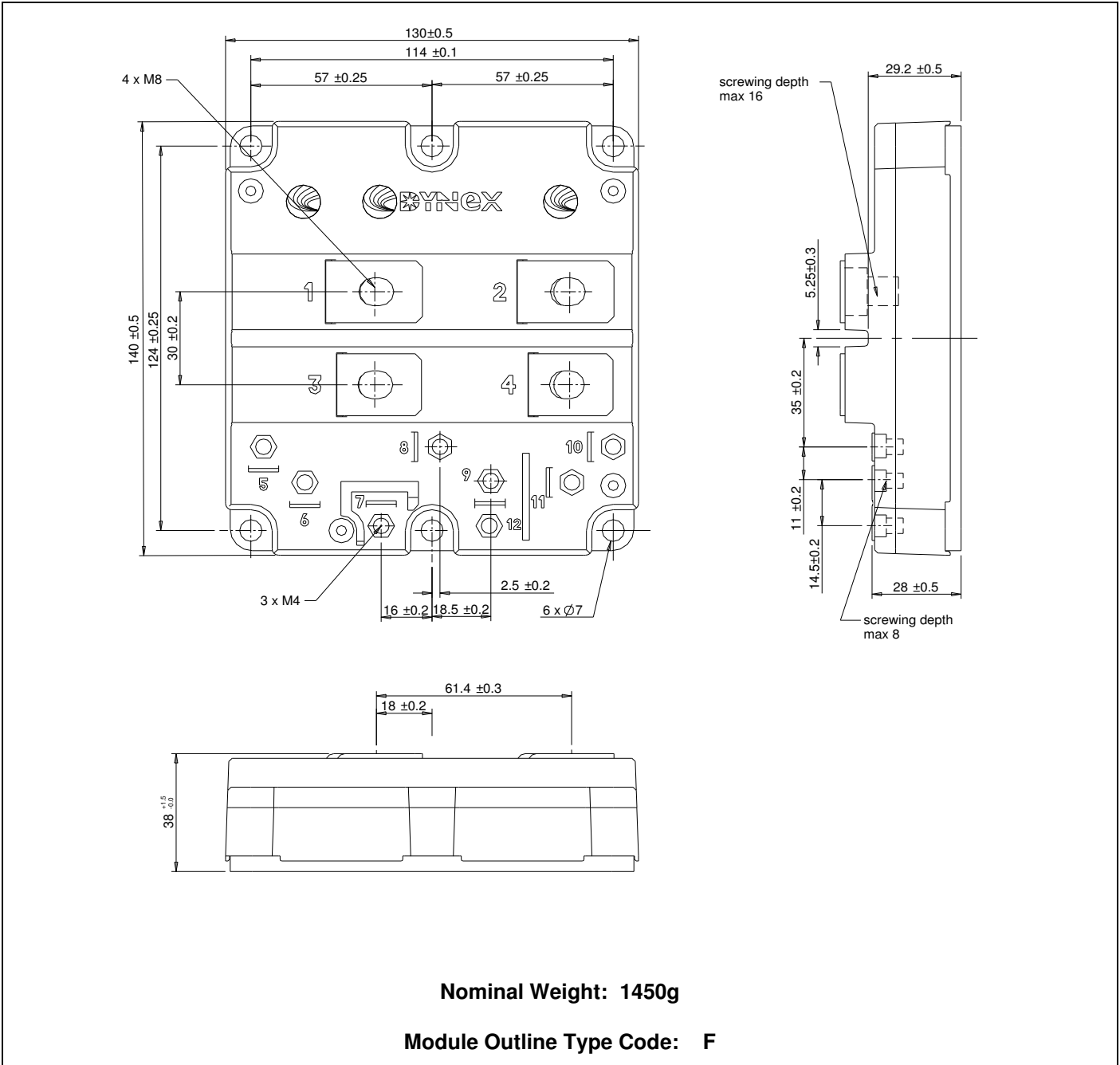


Fig. 6 RBSOA

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.


Fig. 7 Module outline drawing

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Target Information:	This is the most tentative form of information and represents a very preliminary specification. No actual work on the product has been started.
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No Annotation:	The product parameters are fixed and the product is available to datasheet specification.

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